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IN THE CLAIMS

Please amend claims 19-20 and add claims 21-26 as follows:

17. (amended) A method of fabricating a semiconductor wafer, comprising:

(a) subjecting said semiconductor wafer to a pressure; and

(b) measuring said pressure said semiconductor is subjected to with a pressure measurement device supported on said semiconductor wafer, said pressure measurement device including (i) a capacitor, (ii) capacitance measurement circuitry electrically coupled to said capacitor, and (iii) capacitance to pressure conversion circuitry electrically coupled to said capacitance measurement circuitry, and further including converting a capacitance of said capacitor to a pressure with said capacitance to pressure conversion circuitry.

Please cancel claim 18, without prejudice.

19. (amended) The method of claim 17, wherein said pressure measurement device includes capacitance to pressure conversion circuitry, said method further comprising:

(c) storing said pressure in pressure data storage circuitry supported on said semiconductor wafer, said pressure data storage circuitry being electrically coupled to said capacitance to pressure conversion circuitry.

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20. (amended) The method of claim 17, wherein said pressure measurement device includes capacitance to pressure conversion circuitry, said method further comprising:

(c) transmitting a signal indicative of said pressure to a receiver with transmitter circuitry which is (i) electrically coupled to said capacitance to pressure conversion circuitry and (ii) supported on said semiconductor wafer.

21. (new) The method of claim 19, further comprising:

(d) associating said pressure stored in said pressure data storage circuitry with current time via current time circuitry supported on said semiconductor wafer, said pressure data storage circuitry being electrically coupled to said current time circuitry.

22. (new) The method of claim 21, further comprising:

(c) activating said pressure measurement device via a switch supported on said semiconductor wafer.

23. (new) The method of claim 17, further comprising:

(d) deactivating said arrangement via said switch.

24. (new) The method of claim 23, further comprising:

(c) activating said pressure measurement device via a switch supported on said semiconductor wafer.

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25. (new) The method of claim 17, further comprising, before step (a), forming said capacitor on the semiconductor by fabricating first and second metal plates on the semiconductor, the first and second metal plates separated by a void.

26. (new) The method of claim 25 wherein forming the capacitor on the semiconductor further comprises supporting a protecting layer on the semiconductor wafer so that the capacitor is interposed between said protective layer and said semiconductor wafer.

27. (new) A method of fabricating a semiconductor wafer, comprising:

(a) forming a capacitor on the semiconductor by fabricating first and second metal plates on the semiconductor wafer, the first and second metal plates separated by a void;

(b) subjecting said semiconductor wafer to a pressure; and

(c) measuring said pressure said semiconductor wafer is subjected to using the capacitor.

28. (new) The method of claim 27 wherein forming the capacitor on the semiconductor further comprises supporting a protecting layer on the semiconductor wafer so that the capacitor is interposed between said protective layer and said semiconductor wafer.